

HIGH VOLTAGE ULTRAFAST RECTIFIER

MAIN PRODUCT CHARACTERISTICS

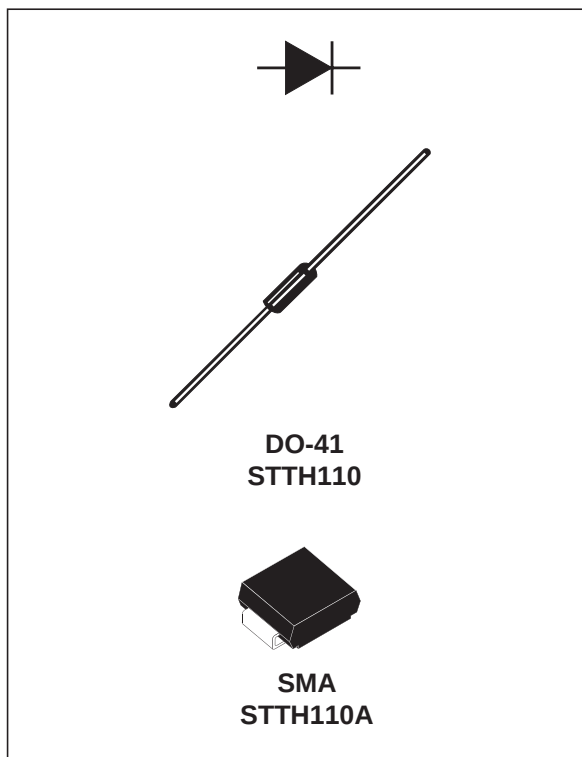
$I_{F(AV)}$	1 A
V_{RRM}	1000 V
$T_j \text{ (max)}$	175 °C
$V_F \text{ (max)}$	1.42 V

FEATURES AND BENEFITS

- Low forward voltage drop
- High reliability
- High surge current capability
- Soft switching for reduced EMI disturbances
- Planar technology

DESCRIPTION

The STTH110, which is using ST ultrafast high voltage planar technology, is specially suited for free-wheeling, clamping, snubbing, demagnetization in power supplies and other power switching applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			1000	V
V _(RMS)	RMS voltage			700	V
I _{F(AV)}	Average forward current	TI = 100°C δ=0.5	DO-41	1	A
		TI = 125°C δ=0.5	SMA	1	
I _{FSM}	Forward surge current t = 8.3 ms		DO-41	20	A
			SMA	18	
T _{stg}	Storage temperature range			- 50 + 175	°C
T _j	Maximum operating junction temperature			+ 175	°C

THERMAL PARAMETERS

Symbol	Parameter			Value	Unit
$R_{th(j-l)}$	Junction to lead	L = 10 mm	DO-41	45	°C/W
			SMA	30	
$R_{th(j-a)}$	Junction to ambient	L = 10 mm	DO-41	110	

STATIC ELECTRICAL CHARACTERISTICS

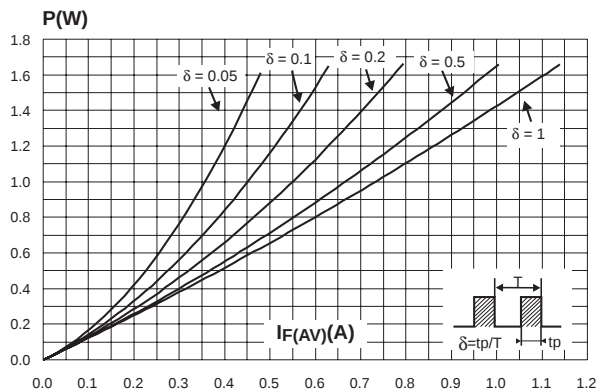
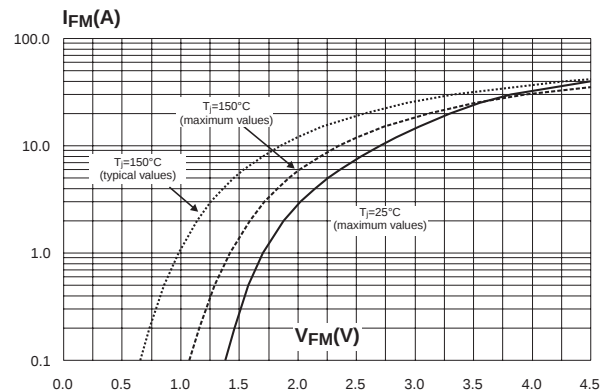
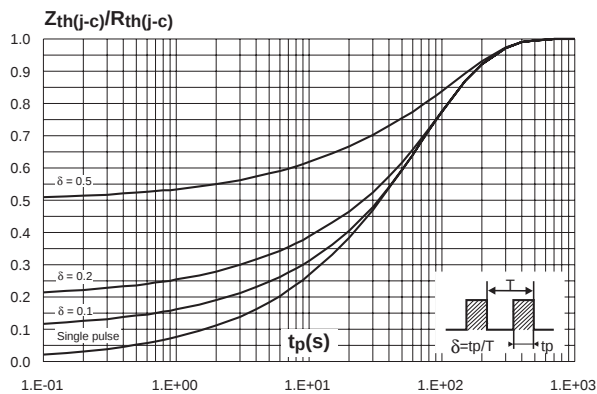
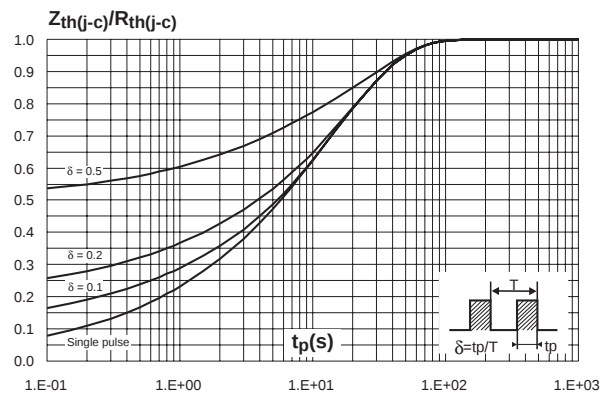
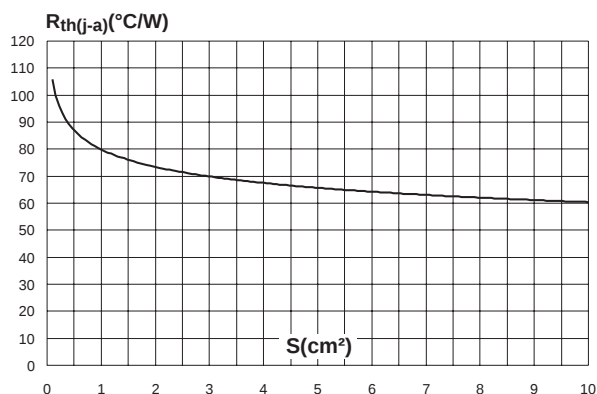
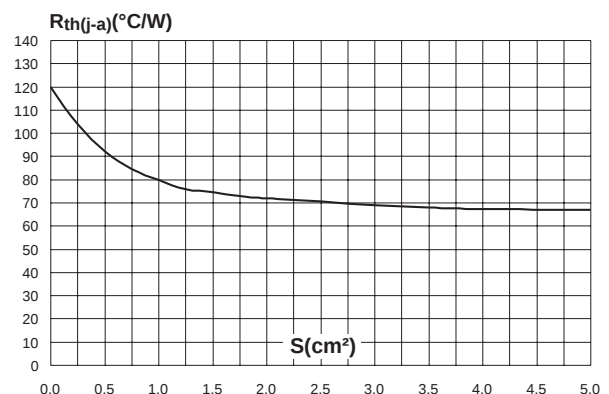
Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R	Reverse leakage current	$V_R = 1000V$	$T_j = 25^\circ C$			10	μA
			$T_j = 125^\circ C$			50	
V_F	Forward voltage drop	$I_F = 1 A$	$T_j = 25^\circ C$			1.7	V
			$T_j = 150^\circ C$		0.98	1.42	

To evaluate the maximum conduction losses use the following equation :

$$P = 1.20 \times I_{F(AV)} + 0.225 \times I_F^2 (RMS)$$

DYNAMIC ELECTRICAL CHARACTERISTICS

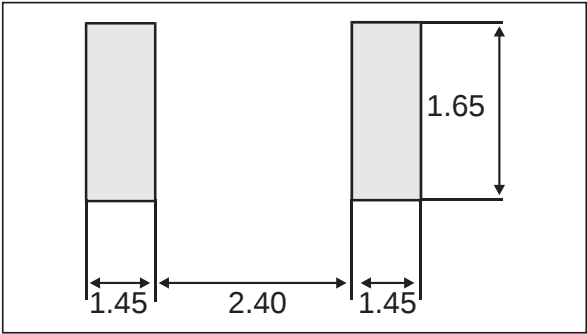
Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 0.5 A$ $I_{rr} = 0.25 A$ $I_R = 1A$	$T_j = 25^\circ C$			75	ns
t_{fr}	Forward recovery time	$I_F = 1 A$ $dI_F/dt = 50 A/\mu s$ $V_{FR} = 1.1 \times V_{Fmax}$	$T_j = 25^\circ C$			300	ns
V_{FP}	Forward recovery voltage					18	V

Fig. 1: Conduction losses versus average current.**Fig. 2:** Forward voltage drop versus forward current.**Fig. 3-1:** Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4, $L_{leads} = 10mm$) (DO-41).**Fig. 3-2:** Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4) (SMA).**Fig. 4-1:** Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: $35\mu m$) (DO-41).**Fig. 4-2:** Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: $35\mu m$) (SMA).

PACKAGE MECHANICAL DATA
SMA

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.70	0.075	0.106
A2	0.05	0.20	0.002	0.008
b	1.25	1.65	0.049	0.065
c	0.15	0.41	0.006	0.016
E	4.80	5.60	0.189	0.220
E1	3.95	4.60	0.156	0.181
D	2.25	2.95	0.089	0.116
L	0.75	1.60	0.030	0.063

FOOTPRINT (in millimeters)



PACKAGE MECHANICAL DATA

DO-41

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
C	28		1.102	
D	0.712	0.863	0.028	0.034

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH110	STTH110	DO-41	0.34 g	2000	Ammopack
STTH110A	H10	SMA	0.068 g	5000	Tape & reel
STTH110RL	STTH110	DO-41	0.34 g	5000	Tape & reel

- Epoxy meets UL 94,V0

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